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GROWTH OF TRANSPARENT As Well As FLEXIBLE THIN MOVIE FROM HYBRID ALLOY USING DEPOSITION BY DISSIPATION METHOD

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ABSTRACT:

This work presents the fabrication process of an intelligent thin film from a hybrid compound to realize transparency and flexibility characteristics. Various delicate operations are encountered during preparation of the film such as exposition to radiations and baking in vacuum oven for many times. The built film with specifics materials improves the performances. The phase quality depends on the type of additives materials during preparation. The band gap of the film is controlled to permit reliability of the fabricated film and endurement of temperature variations. The fabricated thin film can be an alternative and crucial solution for many smart devices that are influenced by blazing and glazing limits. This work also parallelly represent the characteristics such as electrical impedance in function of temperature and optical reflection coefficient.

Keywords: HPLC, PDA, stability indication method, drug.

1. INTRODUCTION:

The nanotechnology provides many routes includes transistor thin-film fabrication. It constitutes the core of smart device especially in electronic memory and liquid crystal display manufacturing. Also, this technology is widely used in many fields such as photovoltaic and advanced electronic devices, etc., [1]. In this work we studied a hybrid compound where many elements are implemented precisely (Al, Pb, ZnO). The alloy has native tendency to n-type conductivity and suitable thermal conductivity. Moreover, the chemical kinds are easy to prepare and available. The materials that are used here are limited due to problems of glazing and blazing and there are hard steps during preparation. The process of semiconductor is based on either insulant or conductor and changing the content using impurities to adjust band gap which is relied to charge carrier density [2]. We noticed from literature that the materials properties and their compositions have influence on performances of alloys so that the choice of materials is delicate [3].

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Different methods are adopted to film manufacturing processes either physical or chemical ones such as, deposition techniques, laser deposition, sputtering evaporation, chemically based nonvacuum deposition techniques and electrochemical deposition [4]. Our work is based on chemical evaporation and the goal is to ensure high quality of the film that has strong challenge with actuals films with the transparency and flexibility characteristics. In addition to that the materials (Al, Pb, ZnO) are scaled to reduced potential range, electrical impedance and stable under oven phases changes like some thin films with reference to the literature [5]. Many researches are taking place in nanotechnologies, but the problems go with solid phase like smashing and bad quality due to restriction of optical and chemical properties [6-8]. Therefore, we are giving here an alternative method by changing the optical and morphological intrinsic properties of the compound [9]. We fabricated samples of thin film with appropriate performances especially flexibility, transparency and induration of thermal variations. The potential of a single element is hard to ensure suitable semiconductor.

2. RELATED STUDY:

We used a hybrid alloy (Al, Pb, ZnO) to resolve this restriction. Therefore, we kept adequate potential gap and make easy the process of deposition by boosting the technique using catalysts such as acid medium and high temperature oven. Moreover, a good correspondence remarked betweenthe Pb and ZnO that leads for others complexations [10]. The studied sample is rich in Al and poor on both ZnO and Pb. The chemical composition depends on the abundance of each elements in the fabricated film. Yet, the quality of thin film is relied to the composition, so the experiment is based on many samples to make comparisons as inspired from example with different composition ratios [11,12]. The developed thin film may be a novel one for nanotechnology. The improvement of optical and morphological characteristics is obtained subsequently in the experimental results. The film is qualified as a privileged one with its smallest size around few nanometers. Moreover, it has wonderful optical qualities. The solubility of these materials in diluted acid leads towards narrow superposition of layers with

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high performances. It ensures a suitable mobility and conductivity by doping diffusion to generate electron-holes [13,14] that are necessary to the conduction of junctions. However, we noted that during the steps of thin film fabrication there are many holdbacks due phenomena of crystallization and oxidation. Therefore, the chemical composition and temperature of baking were adjusted upto the results obtained satisfactory. In fact, the goal is to keep high performances obtained directly after preparation and doping whatever the variations of ambient conditions more specifically the temperature variations. If the lead (Pb) is included in Si, Ge, Sn and C family group, it can provide various uses. Therefore, the semiconductors based on these elements are characterized by low potential and adequate band gap. So, this element used as its derivative PbCl2 but with weak ratio to minimize toxic effect.

3. PROPOSED METHODOLOGY:

ZnO is a smart material that is often implemented in latest technologies. It is an inorganic compound, insoluble in water, and it has used as a large additive in numerous materials and products including rubbers, plastics, ceramics, glass and lubricants [15]. For example, it used in adhesives, sealants, foods, batteries and ferrites. Although, it is abundant naturally as the form of mineral zincite but most of the zinc oxides are produced synthetically [16]. ZnO has a wide-bandgap semiconductor of the II-VI semiconductor group. By adding impurities of aluminium and the privilege of native doping the semiconductor has tendency into n-type due to oxygen vacancies or zinc interstitials [17]. This work used it to get transparency, high electron mobility and wide band gap, those properties are valuable in emerging applications such as transparent electrodes in liquid crystal displays, and electronics as thin-film transistors and light emitting diodes. The chemical deposition processes are depicted.

The goal of this work is to boost performances of existing thin films by getting transparency and flexibility properties with the manufacturing scale. The core idea is based on changing the phase such as the built of some alloys referred to the literature [18,19]. The composition of aluminium (Al) is rich when compared to the PbCl2 and ZnO to

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obtain the suitable electric impedance. The thin layer of aluminium was put under exposition of UV for 40 min. After that the compound was placed on a substrate of polymers such as polycarbonate to endure drying process inside an oven for 20 min with temperature at 280 °C. After that a transparent and flexible thin film was obtained. The impedance was calculated for various temperatures to confirm the accepted performances of this alloy film as done in previous work [20, 21]. The deposited thin film was rinsed with distilled water and dried in the air. Then, the thin film was ready to be characterized by many techniques such as the reflection to laser beam. The testing voltage 0.8 V applied between two different sides of the film to verify conduction junction. To confirm the elements composition in the specimen thin film, emission of laser beam generated from DVD were readed and worked by 3 V as feed voltage. Then, the reflected voltage difference reveals the chemical composition. The laser beam was characterized by high frequency that reaches 140 TGHz and wavelength at 650 nm.

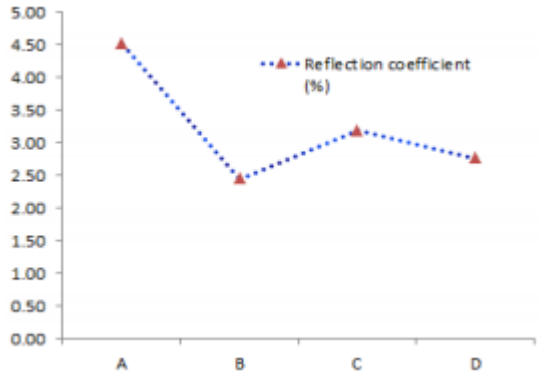

Fig.3.1. Proposed system results.

5. CONCLUSION:

This work is an effective contribution to fabricate thin film with high performances. A competitive thin film has been developed that respond to the size of thickness which is at order of many nanometers. The transparency is an aesthetic side that gives the films as a strong challenge in the field of thin film technologies. Yet, the reliability of these nanostructures ensures that alloys constitute an alternative with thermodynamic quality to the flexibility and morphological structure. The endurance to temperature variations confirm that the films keep stable phase and compact surface when external noises such as oxidation and crystallization are absent. The laser beam analysis processed to determine the electrical

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impedance and optical properties and reveals a promising result.

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